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the second inverse-mode bipolar transistors comprise  
buried layers,  
the first inverse-mode bipolar transistors employ the  
buried layers as emitters,  
the second inverse-mode bipolar transistors employ  
the buried layers as emitters,  
the emitters of the first and second inverse-mode  
bipolar transistors are electrically coupled to each  
other, and

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the collectors of the first and second inverse-mode  
bipolar transistors are electrically coupled to the  
first and second load devices, respectively.

29. A semiconductor device according to claim 28,  
further comprising shielding means for shielding the  
first and second load devices from noise produced  
within the semiconductor substrate.

30. A semiconductor device according to claim 4,  
wherein said shielding means is a doped region of the  
same conduction type as that of said semiconductor  
substrate, and wherein a predetermined voltage is ap-  
plied to said doped region.

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